

Chip Schottky Barrier Diodes

Silicon epitaxial planer type

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds environmental standards of ML-S-19500 / 228
- Low leakage current

Mechanical data

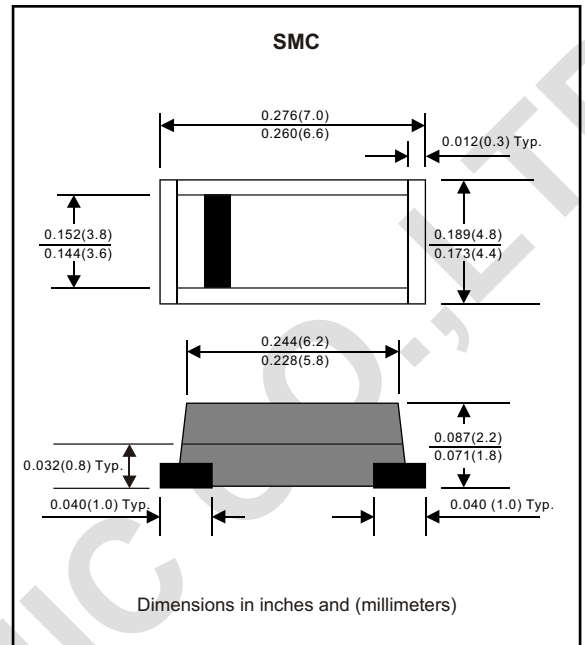
Case : Mottled plastic, JEDEC DO-214AB

Terminals : Solder plated, solderable per MIL-STD-750, Method 2026

Polarity : Indicated by cathode band

Mounting Position : Any

Weight : 0.00585 ounce, 0.195 gm



MAXIMUM RATINGS (AT T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.1	I _O			3.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I _{FSM}			80	A
Reverse current	V _R = V _{RRM} T _A = 25 °C	I _R			0.5	mA
	V _R = V _{RRM} T _A = 125 °C				20	mA
Thermal resistance	Junction to ambient	R _{θJA}		55		°C / w
Diode junction capacitance	f=1MHz and applied 4vDC reverse voltage	C _j		250		pF
Storage temperature		T _{STG}	-55		+150	°C

SYMBOLS	MARKING CODE	V _{RRM} ^{*1} (V)	V _{RMS} ^{*2} (V)	V _R ^{*3} (V)	V _F ^{*4} (V)	Operating temperature (°C)
FM320	SS32	20	14	20	0.55	-55 to +125
FM330	SS33	30	21	30		
FM340	SS34	40	28	40		
FM350	SS35	50	35	50	0.70	-55 to +150
FM360	SS36	60	42	60		
FM380	SS38	80	56	80	0.85	
FM3100	S310	100	70	100		

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

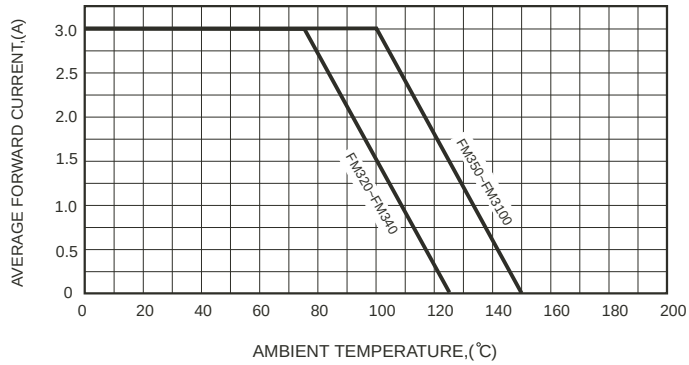


FIG.2-TYPICAL FORWARD CHARACTERISTICS

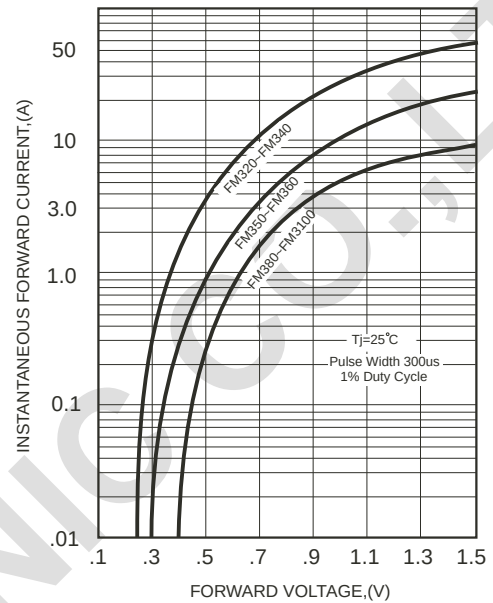


FIG.3-MAXIMUM NON-REPETITIVE FORWARD

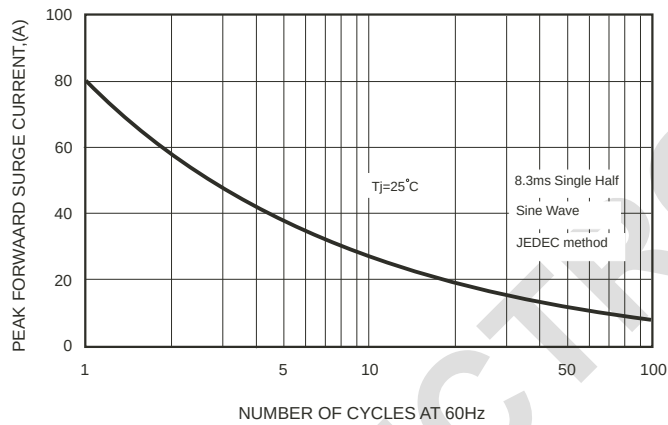


FIG.4-TYPICAL JUNCTION CAPACITANCE

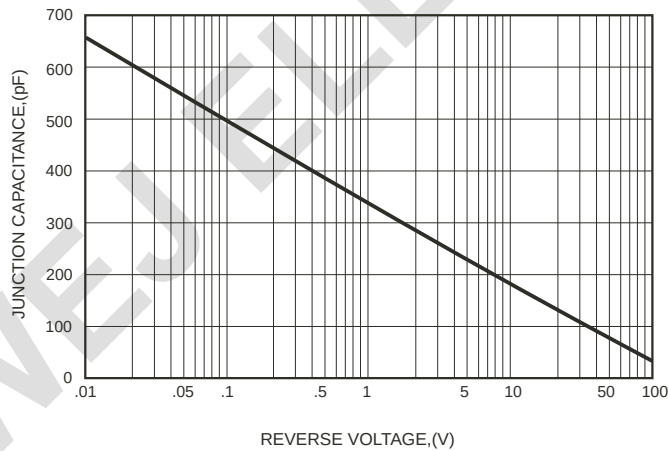


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

